



**TET ESTEL AS**  
ESTONIA

**January**  
**2017**

**Series**  
**TF261-125**

## Fast Stud Mounted Thyristor Type TF261-125

Low on-state and switching losses  
Low reverse recovery charge  
Center amplifying gate

Maximum mean on-state current					$I_{TAV}$	<b>125 A</b>			
Maximum repetitive peak off-state and reverse voltage					$U_{DRM}$	<b>600 ÷ 1400 V</b>			
Turn-off time					$U_{RRM}$				
					$t_q$	<b>20; 25; 32 <math>\mu</math>s</b>			
$U_{DRM}, U_{RRM}, V$	600	700	800	900	1000	1100	1200	1300	1400
Voltage code	6	7	8	9	10	11	12	13	14
$T_{vj}, ^\circ C$	- 60 ÷ 125								

### MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	TF261-125	Conditions
$I_{TAV}$	Mean on-state current	A	125	$T_c=88^\circ C$ , 180° half-sine wave, 50 Hz
$I_{TRMS}$	RMS on-state current	A	196	$T_c=88^\circ C$
$I_{TSM}$	Surge on-state current	kA	3,5 3,7	$T_{vj}=125^\circ C$ $T_{vj}=25^\circ C$ tp=10 ms $U_R=0$
$I^2t$	Limiting load integral	$kA^2s$	61,2 68,4	$T_{vj}=125^\circ C$ $T_{vj}=25^\circ C$
$U_{DRM}, U_{RRM}$	Repetitive peak off-state and reverse voltage	V	600÷1400	$T_j \min \leq T_{vj} \leq T_{jm}$ 180° half-sine wave, 50 Hz Gate open
$U_{DSM}, U_{RSM}$	Non-repetitive peak off-state and reverse voltage	V	660÷1500	$T_j \min \leq T_{vj} \leq T_{jm}$ 180° half-sine wave tp=10 ms, Single pulse Gate open
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current : non - repetitive repetitive	A/ $\mu$ s	800 400	$T_{vj}=125^\circ C$ ; $U_D=0,67 U_{DRM}$ , Gate pulse : 10V, 5 $\Omega$ , 1 $\mu$ s rise time, 10 $\mu$ s
$U_{RGM}$	Peak reverse gate voltage	V	5	$T_j \min \leq T_{vj} \leq T_{jm}$
$T_{stg}$	Storage temperature	$^\circ C$	-60÷80	
$T_{vj}$	Junction temperature	$^\circ C$	-60÷125	

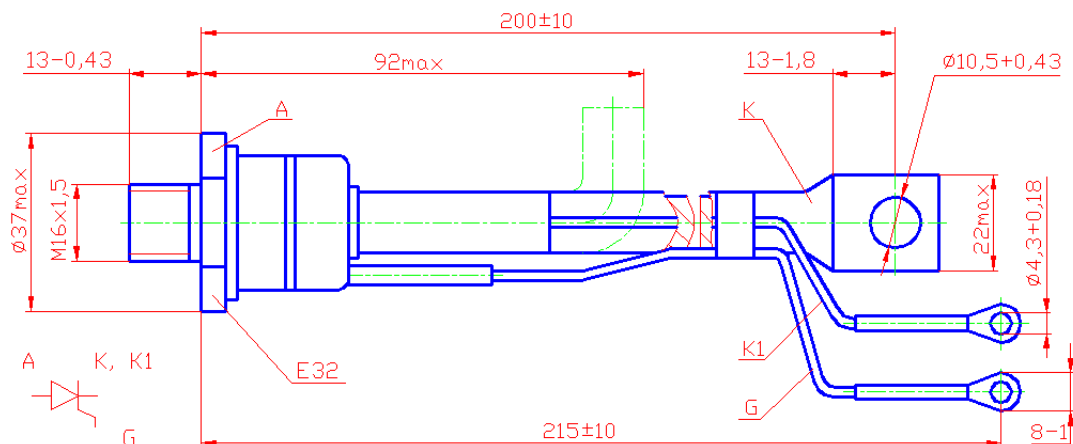
### CHARACTERISTICS

$U_{TM}$	Peak on-state voltage	V	2,2	$T_{vj}=25^\circ C$ , $I_{TM}=3,14 I_{TAV}$
$U_{T(To)}$	Threshold voltage	V	1,45	$T_{vj}=125^\circ C$
$R_T$	On-state slope resistance	m $\Omega$	2,5	1,57 $I_{TAV} < I_T < 4,71 I_{TAV}$
$I_{DRM}$ $I_{RRM}$	Repetitive peak off-state and reverse current	mA	25 25	$T_{vj}=125^\circ C$ , $U_D = U_{DRM}$ $U_R = U_{RRM}$

CHARACTERISTICS				
Symbols and parameters		Units	TF261-125	Conditions
$I_L$	Latching current	A	0,7	$T_{vj}=25^{\circ}\text{C}, U_D=12\text{V}$ Gate pulse : 10V, 5 $\Omega$ , 1 $\mu\text{s}$ rise time, 10 $\mu\text{s}$
$I_H$	Holding current	A	0,3	$T_{vj}=25^{\circ}\text{C}, U_D=12\text{V}$ , Gate open
$U_{GT}$	Gate trigger direct voltage	V	2,5 5,0	$T_{vj}=25^{\circ}\text{C}$ , $T_{vj}=-60^{\circ}\text{C}$
$I_{GT}$	Gate trigger direct current	A	0,25 0,6	$T_{vj}=25^{\circ}\text{C}$ , $T_{vj}=-60^{\circ}\text{C}$
$U_{GD}$	Gate non-trigger direct voltage	V	0,25	$T_{vj}=125^{\circ}\text{C}$ , $U_D = 0,67 U_{DRM}$
$I_{GD}$	Gate non-trigger direct current	mA	10	Direct gate current
$t_{gd}$	Delay time	$\mu\text{s}$	1,4	$T_{vj}=25^{\circ}\text{C}, U_D=500\text{V}$ $I_{TM} = 125 \text{ A}$
$t_{gt}$	Turn-on time	$\mu\text{s}$	3,2	Gate pulse : 10V, 5 $\Omega$ , 1 $\mu\text{s}$ rise time, 10 $\mu\text{s}$
$t_q$	Turn-off time	$\mu\text{s}$	20÷32 25÷40	$T_{vj}=125^{\circ}\text{C}$ , $I_{TM}=125 \text{ A}$ $di_R/dt = 10 \text{ A}/\mu\text{s}$ , $U_R=100\text{V}$ $U_D = 0,67 U_{DRM}$ $du_D/dt=50 \text{ V}/\mu\text{s}$ $du_D/dt=200 \text{ V}/\mu\text{s}$
$Q_{rr}$	Recovered charge	$\mu\text{C}$	165	
$t_{rr}$	Reverse recovery time	$\mu\text{s}$	3,3	$T_{vj}=125^{\circ}\text{C}$ , $I_{TM}=125 \text{ A}$
$I_{rrm}$	Peak reverse recovery current	A	100	$di_R/dt = 50 \text{ A}/\mu\text{s}$ , $U_R=100\text{V}$
$(du_D/dt)_{crit}$	Critical rate of rise of off-state voltage	V/ $\mu\text{s}$	500 1000	$T_{vj}=125^{\circ}\text{C}$ , $U_D = 0,67 U_{DRM}$ Gate open
$R_{thjc}$	Thermal resistance junction to case	$^{\circ}\text{C}/\text{W}$	0,12	Direct current

ORDERING							
	<b>TF</b>	<b>261</b>	<b>125</b>	<b>14</b>	<b>6</b>	<b>6</b>	<b>2</b>
	<b>1</b>	<b>2</b>	<b>3</b>	<b>4</b>	<b>5</b>	<b>6</b>	<b>7</b>

1. Fast thyristor.
2. Design version.
3. Mean on-state current, A.
4. Voltage code (14=1400 V).
5. Critical rate of rise of off-state voltage ( $6 \geq 500 \text{ V}/\mu\text{s}$ ,  $7 \geq 1000 \text{ V}/\mu\text{s}$ ).
6. Group of turn-off time ( $du_D/dt=50 \text{ V}/\mu\text{s}$ ,  $4 \leq 32 \mu\text{s}$ ,  $5 \leq 25 \mu\text{s}$ ,  $6 \leq 20 \mu\text{s}$ ).
7. Group of turn-on time ( $2 \leq 3,2 \mu\text{s}$ ).



Tightening torque : 24 ÷ 36 Nm  
Weight : 260 grams